

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

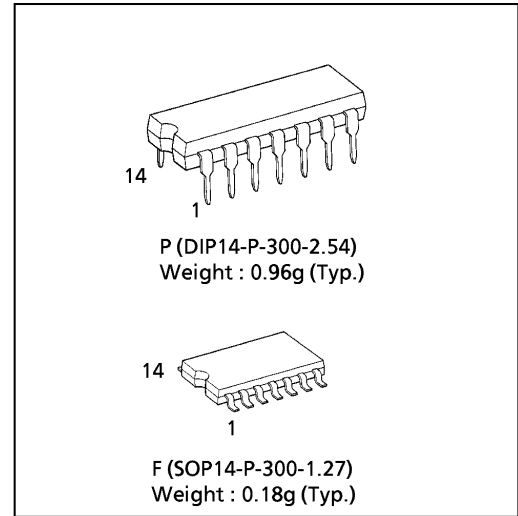
# TC74HCT7007AP, TC74HCT7007AF

## HEX BUFFER

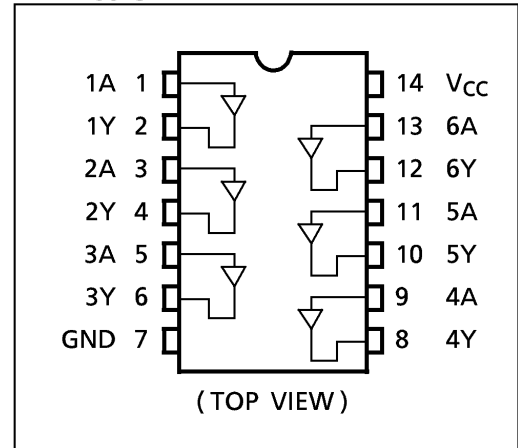
The TC74HCT7007A is a high speed CMOS BUFFER fabricated with silicon gate C<sup>2</sup>MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. The inputs are compatible with TTL, NMOS and CMOS output voltage levels. The internal circuit is composed of 4 stages including a buffer output, which provides high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### FEATURES :

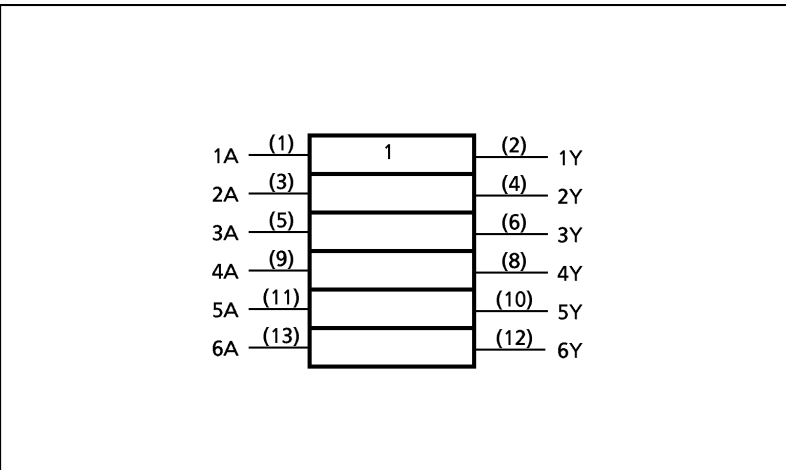
- High Speed..... $t_{pd} = 11\text{ns}(\text{typ.})$  at  $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 1\mu\text{A}(\text{Max.})$  at  $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs....  $V_{IH} = 2\text{V}(\text{Min.})$   
 $V_{IL} = 0.8\text{V}(\text{Max.})$
- Wide Interfacing ability..... LSTTL, NMOS, CMOS
- Output Drive Capability..... 10 LSTTL Loads
- Symmetrical Output Impedance...  $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays....  $t_{pLH} \approx t_{pHL}$
- Pin and Function Compatible with 74LS07



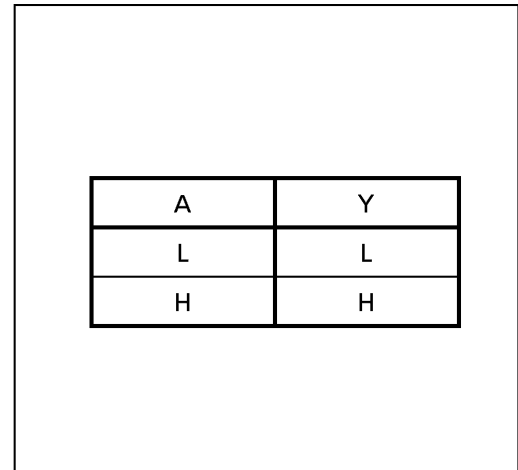
### PIN ASSIGNMENT



### IEC LOGIC SYMBOL



### PIN ASSIGNMENT



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## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	$V_{CC}$	-0.5~7	V
DC Input Voltage	$V_{IN}$	-0.5~ $V_{CC}+0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5~ $V_{CC}+0.5$	V
Input Diode Current	$I_{IK}$	$\pm 20$	mA
Output Diode Current	$I_{OK}$	$\pm 20$	mA
DC Output Current	$I_{OUT}$	$\pm 25$	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	$\pm 50$	mA
Power Dissipation	$P_D$	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	$T_{stg}$	-65~150	°C

\*500mW in the range of  $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$ . From  $T_a = 65^{\circ}\text{C}$  to  $85^{\circ}\text{C}$  a derating factor of  $-10\text{mW}/^{\circ}\text{C}$  shall be applied until 300mW.

## RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{CC}$	4.5~5.5	V
Input Voltage	$V_{IN}$	0~ $V_{CC}$	V
Output Voltage	$V_{OUT}$	0~ $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40~85	°C
Input Rise and Fall Time	$t_r, t_f$	0~500	ns

## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}$ (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	$V_{IH}$		4.5 ┆ 5.5	2.0	—	—	2.0	—	V	
Low - Level Input Voltage	$V_{IL}$		4.5 ┆ 5.5	—	—	0.8	—	0.8	V	
High - Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -20 \mu\text{A}$	4.5	4.4	4.5	—	4.4	—	V
			$I_{OH} = -4 \text{ mA}$	4.5	4.18	4.31	—	4.13	—	
Low - Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 20 \mu\text{A}$	4.5	—	0.0	0.1	—	0.1	V
			$I_{OL} = 4 \text{ mA}$	4.5	—	0.17	0.26	—	0.33	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	$\pm 0.1$	—	$\pm 1.0$	$\mu\text{A}$	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	5.5	—	—	1.0	—	10.0	mA	
	$I_C$	PER INPUT: $V_{IN} = 0.5\text{V}$ or $2.4\text{V}$ OTHER INPUT: $V_{CC}$ or GND	5.5	—	—	2.0	—	2.9		

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AC ELECTRICAL CHARACTERISTICS (  $C_L = 15\text{pF}$ ,  $V_{CC} = 5\text{V}$ ,  $T_a = 25^\circ\text{C}$ , Input  $t_r = t_f = 6\text{ns}$  )

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	$t_{TLH}$		—	6	12	ns
	$t_{THL}$					
Propagation Delay Time	$t_{pLH}$		—	11	17	
	$t_{pHL}$					

AC ELECTRICAL CHARACTERISTICS (  $C_L = 50\text{pF}$ , Input  $t_r = t_f = 6\text{ns}$  )

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ\text{C}$			$T_a = -40\sim 85^\circ\text{C}$		UNIT	
			$V_{CC}(\text{V})$	MIN.	TYP.	MAX.	MIN.		MAX.
Output Transition Time	$t_{TLH}$		4.5	—	8	15	—	19	ns
	$t_{THL}$		5.5	—	7	14	—	18	
Propagation Delay Time	$t_{pLH}$		4.5	—	14	23	—	28	
	$t_{pHL}$		5.5	—	12	21	—	26	
Input Capacitance	$C_{IN}$		—	5	10	—	10	pF	
Power Dissipation Capacitance	$C_{PD}(1)$		—	22	—	—	—		

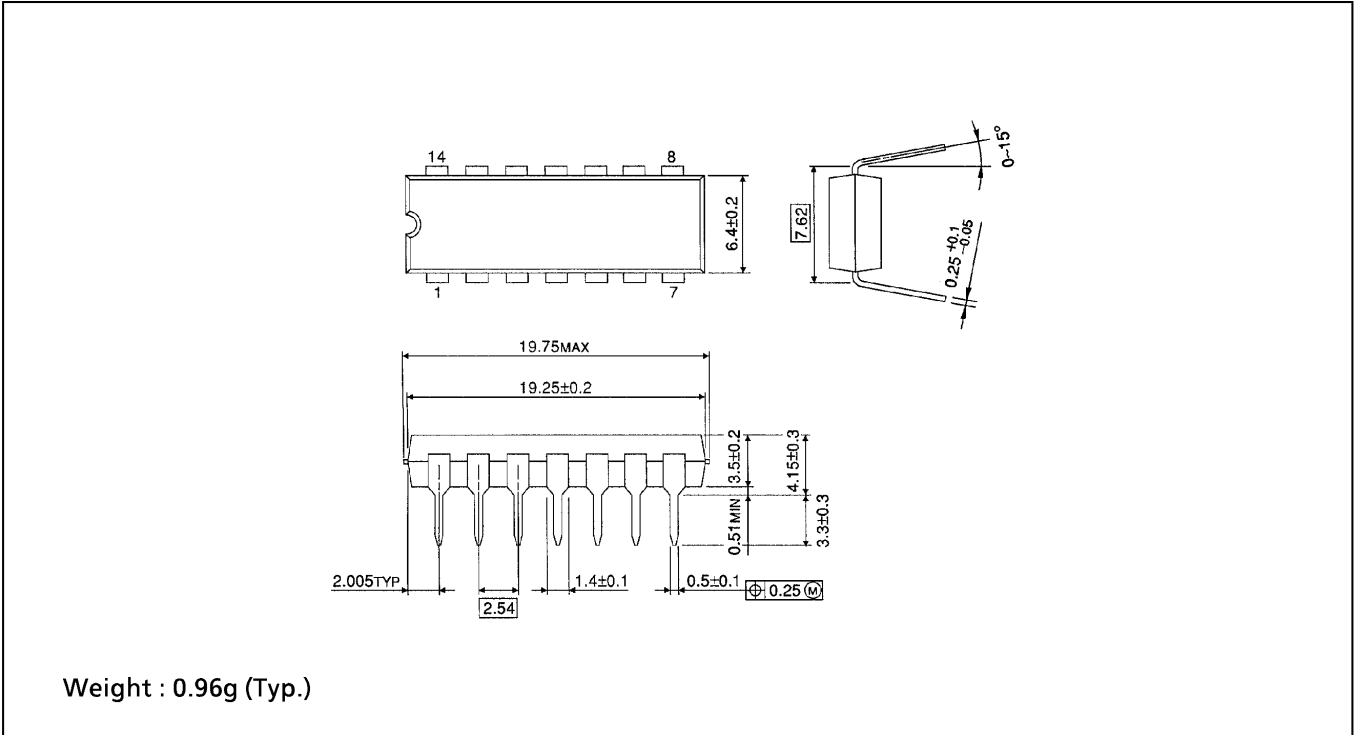
Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per Gate)}$$

DIP 14PIN OUTLINE DRAWING (DIP14-P-300-2.54)

Unit in mm



SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm

